



Attorney's Docket No.: 07977-107002 / US3194/3205/3215D1

THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Yamazaki, et al. Art Unit : 2811  
Serial No.: 09/814,255 Examiner : Ori Nadav  
Filed : March 21, 2001  
Title : SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD

BOX AF

Commissioner for Patents  
Washington, D.C. 20231

RESPONSE

In response to the final action mailed September 4, 2002,  
please amend the application as follows:

In the title:

Please amend the title:

--SEMICONDUCTOR DEVICE HAVING A RELIABLE CONTACT--

In the specification:

Please replace the paragraph beginning at page 5, lines 2-3  
with the following rewritten paragraph:

--To complete the contact hole 104, it is necessary to  
etch the interlayer insulating film 103 which may be a silicon  
oxide film, a silicon nitride film, a silicon oxynitride film,  
or the like, and then etch the anodic oxide film 102.--

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this  
correspondence is being deposited with the  
United States Postal Service as first class mail  
with sufficient postage on the date indicated  
below and is addressed to the Commissioner for  
Patents, Washington, D.C. 20231.

Date of Deposit January 3, 2003

Signature

Tobi Terry

Typed or Printed Name of Person Signing  
Certificate

TECHNOLOGY CENTER 2800  
JAN 13 2003  
RECEIVED  
#10/c  
1-15-03  
J. Smith

do not  
encl  
on